



PSMN1R6-30MLH

N-channel 30 V, 1.9 mΩ logic level MOSFET in LFAK33
using NextPowerS3+ Technology

13 March 2018

Preliminary data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFAK33 package. NextPowerS3+ technology delivers low R_{DSon} , low I_{DSS} leakage and high efficiency. Rated to 160 A and optimised for DC load switch and hot-swap applications.

2. Features and benefits

- Optimised for low R_{DSon}
- Low leakage < 1 μ A at 25 °C
- Optimised for 4.5 V gate drive
- 160 A rated
- High reliability copper-clip bonded and solder die attach LFAK33 package
- Qualified to 175 °C
- Exposed leads for optimal visual solder inspection

3. Applications

- DC switch / load switch
- USB-PD and fast-charge
- Battery protection
- OR-ing and hot-swap
- Synchronous rectifier in AC-DC and DC-DC applications
- BLDC motor control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	[1]	-	160	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	-	106	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	2.02	2.6	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.55	1.9	mΩ

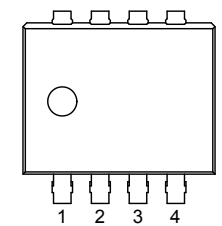
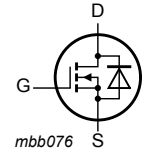
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}$; $V_{DS} = 15\text{ V}$; $V_{GS} = 4.5\text{ V}$; Fig. 12 ; Fig. 13	-	7	-	nC
$Q_{G(\text{tot})}$	total gate charge		-	20	-	nC
Source-drain diode						
S	softness factor	$I_S = 20\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 15\text{ V}$; Fig. 16	-	0.7	-	

[1] 160A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R6-30MLH	LFAK33	Plastic single ended surface mounted package (LFAK33); 8 leads	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R6-30MLH	1H630L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	30	V

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Symbol	Parameter	Conditions	Min	Max	Unit	
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	30	V	
V _{GS}	gate-source voltage		-20	20	V	
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 1	-	106	W	
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2	[1]	-	160	A
		V _{GS} = 10 V; T _{mb} = 100 °C; Fig. 2		-	116	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; Fig. 3	-	640	A	
T _{stg}	storage temperature		-55	175	°C	
T _j	junction temperature		-55	175	°C	
T _{sid(M)}	peak soldering temperature		-	260	°C	

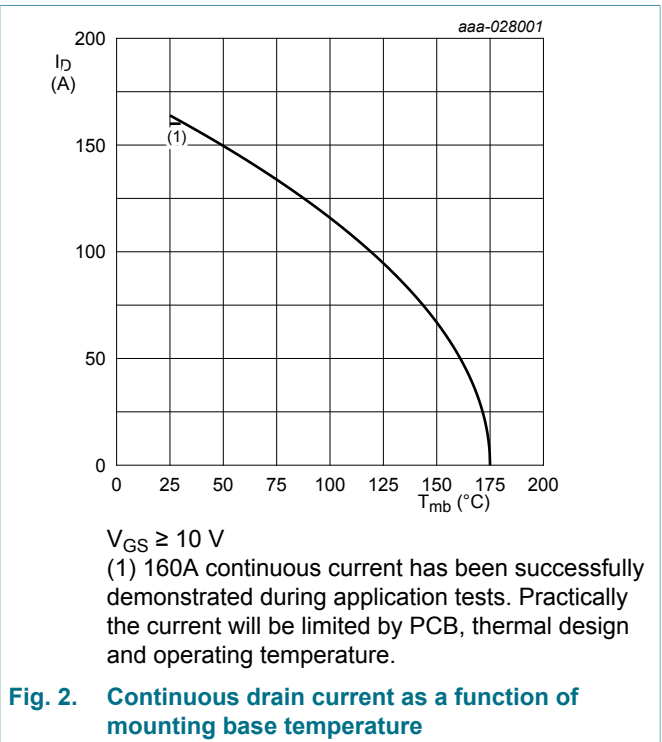
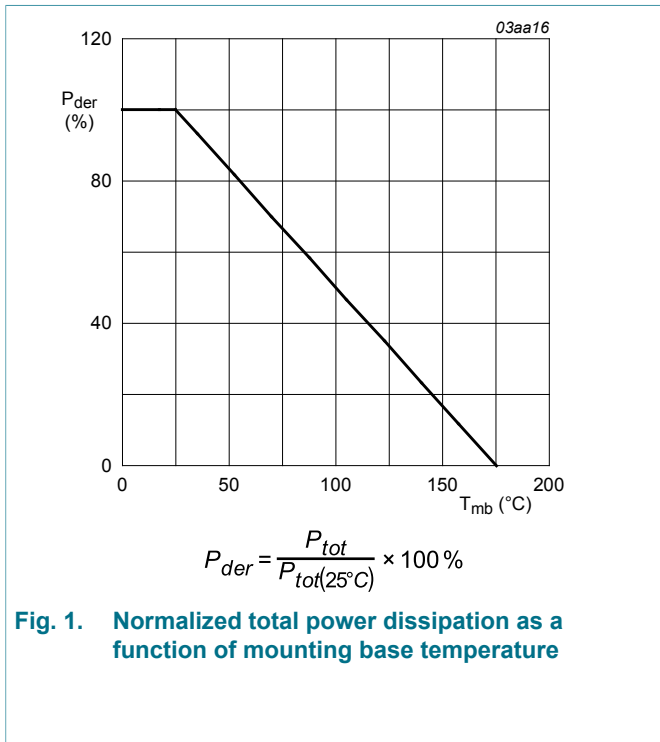
Source-drain diode

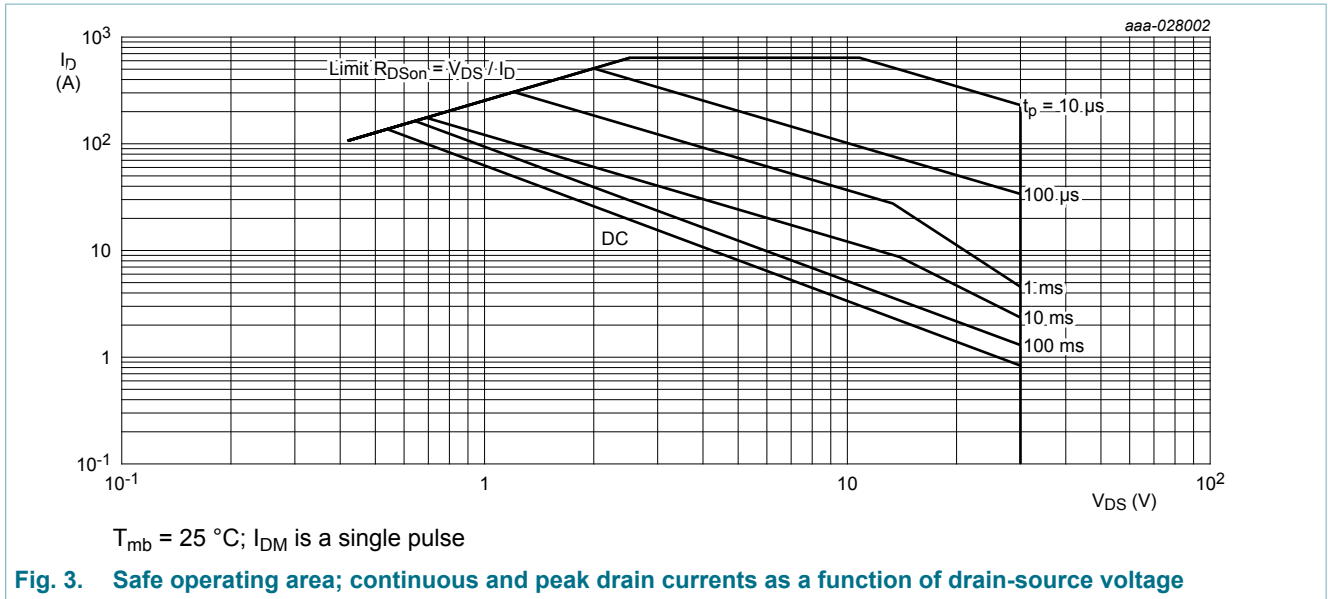
I _S	source current	T _{mb} = 25 °C	-	88	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	640	A

Avalanche ruggedness

E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 25 A; V _{sup} ≤ 30 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; t _p = 797 μs	-	388	mJ
I _{AS}	non-repetitive avalanche current	V _{sup} ≤ 100 V; V _{GS} = 10 V; T _{j(init)} = 25 °C; R _{GS} = 50 Ω	[2]	47	A

- [1] 160A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test

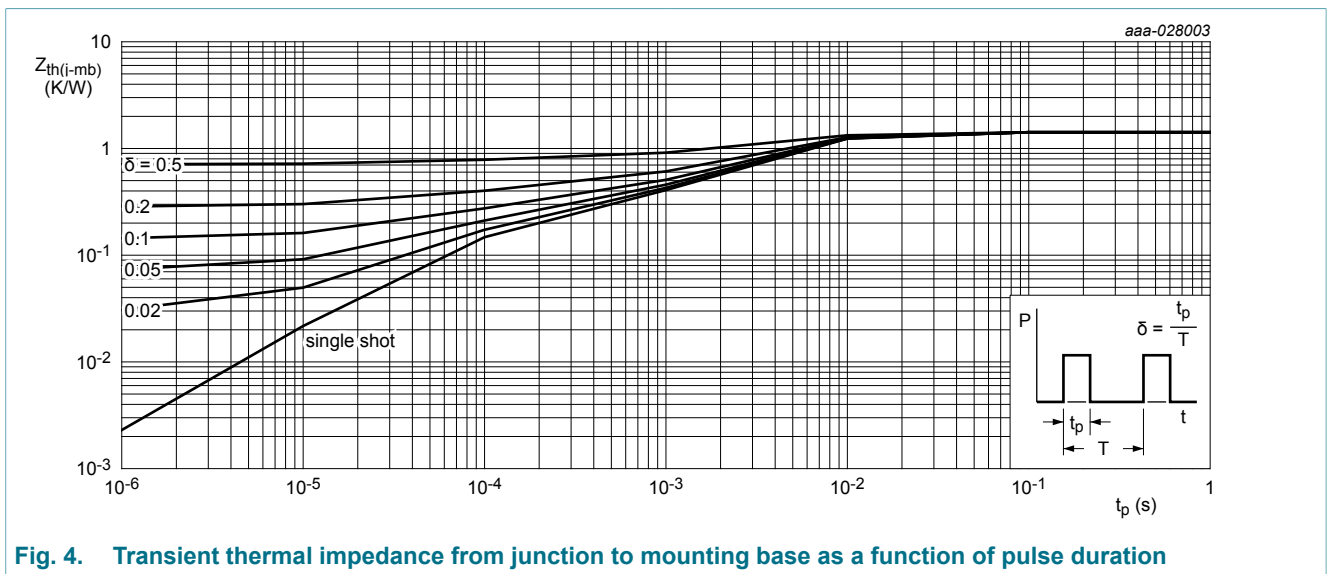


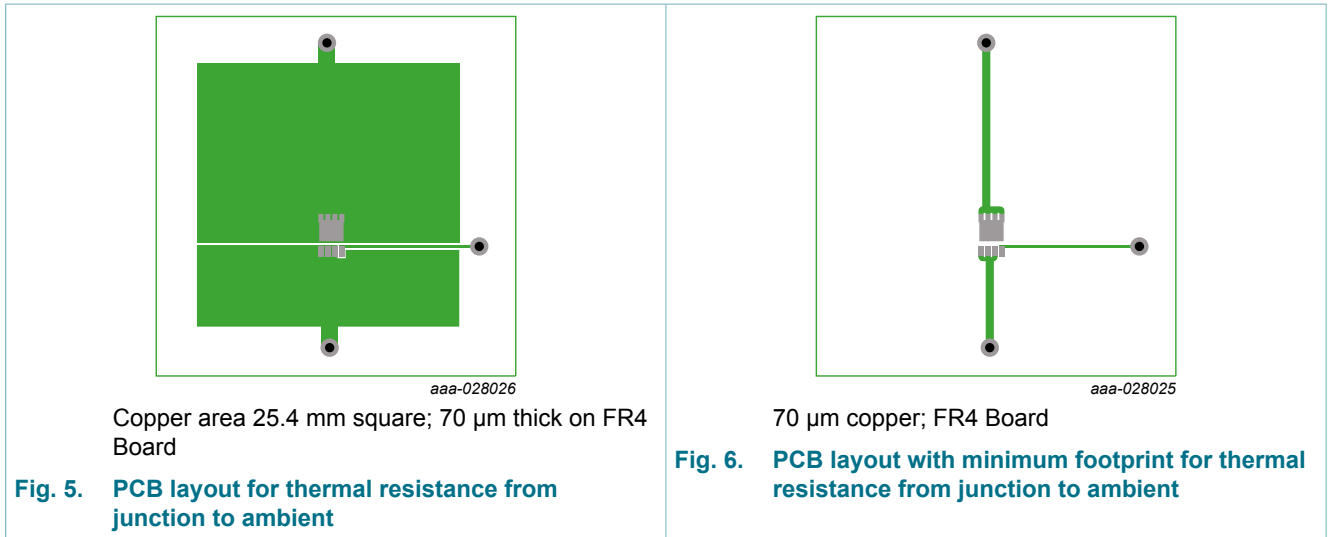


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	1.12	1.42	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	50	-	K/W
		Fig. 6	-	130	-	K/W





10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.2	1.6	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	-3.8	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	2.2	-	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 10	-	2.02	2.6	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C;$ Fig. 11	-	-	4.77	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 10	-	1.55	1.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C;$ Fig. 11	-	-	3.48	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$	-	3.3	-	Ω

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12 ; Fig. 13	-	41	-	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12 ; Fig. 13	-	20	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	21	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12 ; Fig. 13	-	5.7	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	3.6	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.1	-	nC
Q _{GD}	gate-drain charge		-	7	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; Fig. 12 ; Fig. 13	-	2.6	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 14	-	2369	-	pF
C _{oss}	output capacitance		-	758	-	pF
C _{rss}	reverse transfer capacitance		-	217	-	pF
t _{d(on)}	turn-on delay time		V _{DS} = 15 V; R _L = 0.6 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 5 Ω	-	17	-
t _r	rise time		-	34	-	ns
t _{d(off)}	turn-off delay time		-	32	-	ns
t _f	fall time		-	24	-	ns
Q _{oss}	output charge		V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	18.7	-
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 20 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 15	-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 15 V	-	27.6	-	ns
Q _r	recovered charge	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 15 V; Fig. 16	[1]	21.8	-	nC
t _a	reverse recovery rise time		-	16.4	-	ns
t _b	reverse recovery fall time		-	11.2	-	ns
S	softness factor		-	-	0.7	-

[1] includes capacitive recovery

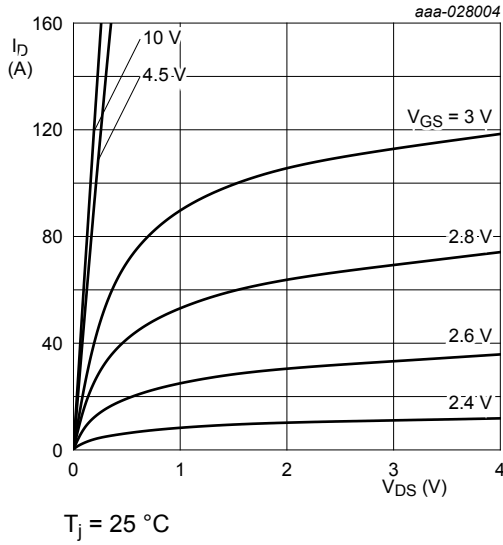


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

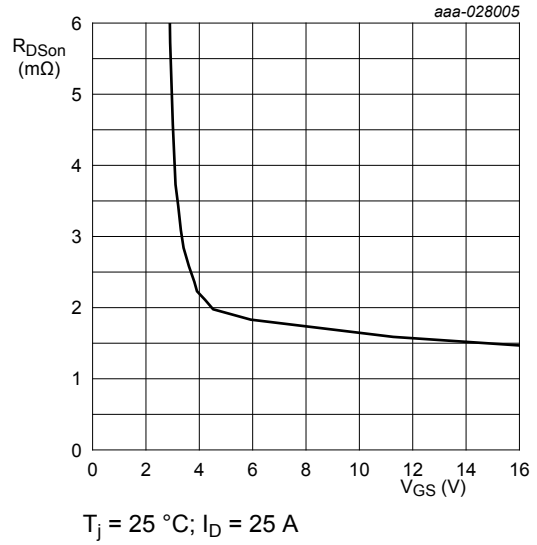


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

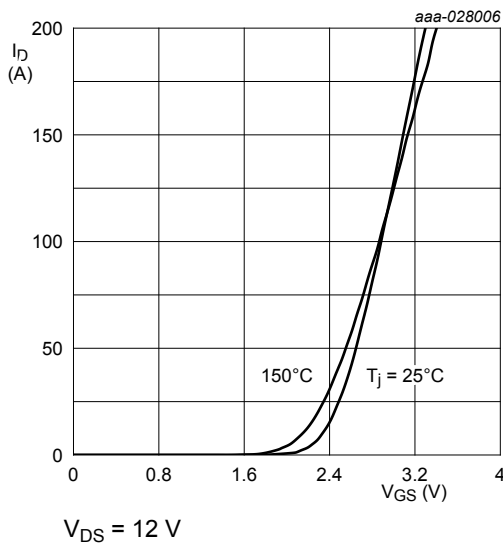


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

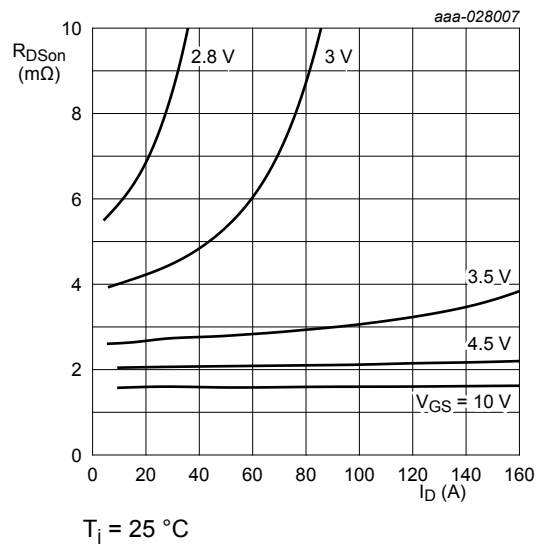
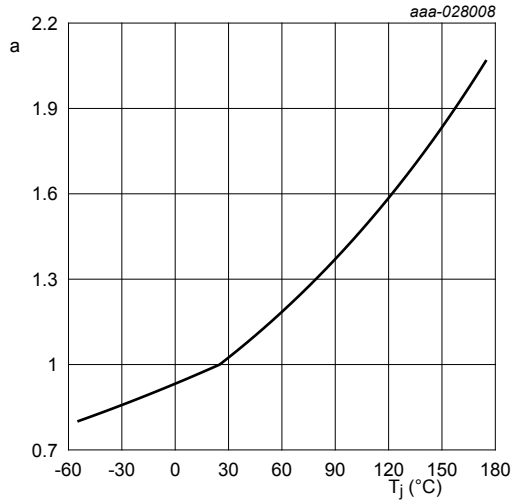
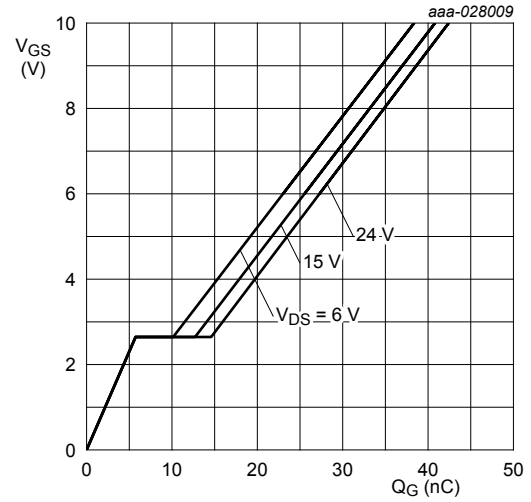


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature



$T_j = 25^{\circ}\text{C}; I_D = 25\text{ A}$

Fig. 12. Gate-source voltage as a function of gate charge; typical values

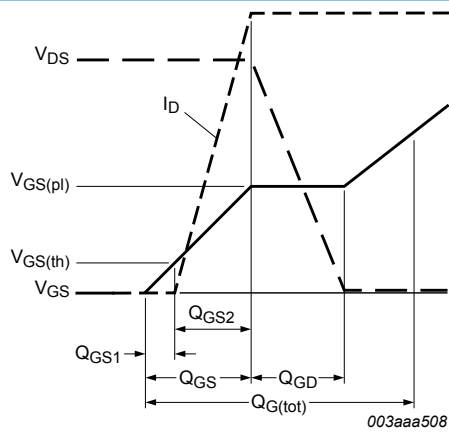
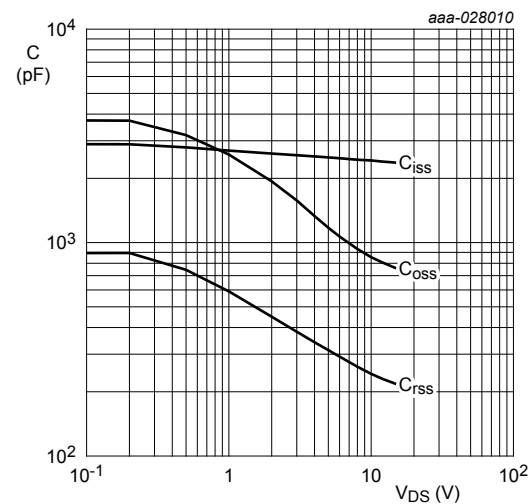


Fig. 13. Gate charge waveform definitions



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

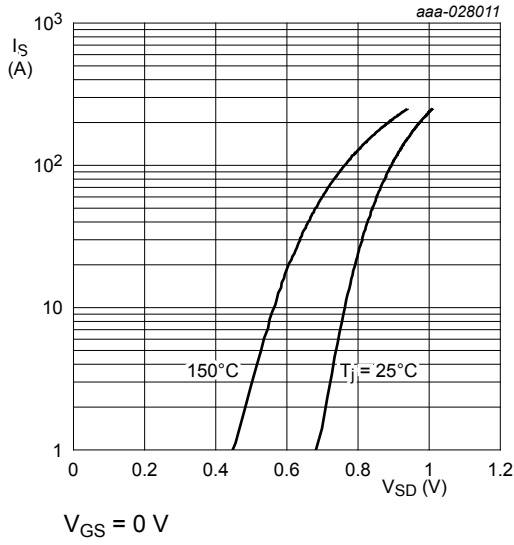


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

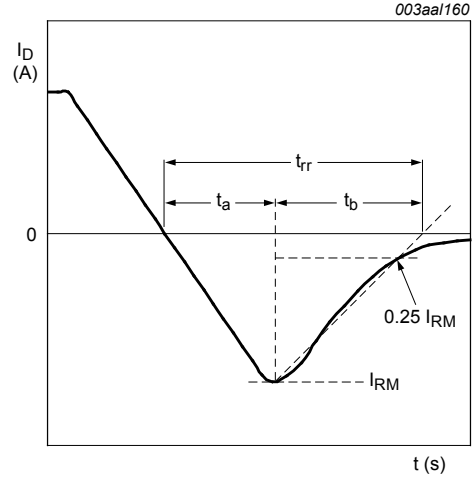


Fig. 16. Reverse recovery timing definition

11. Package outline

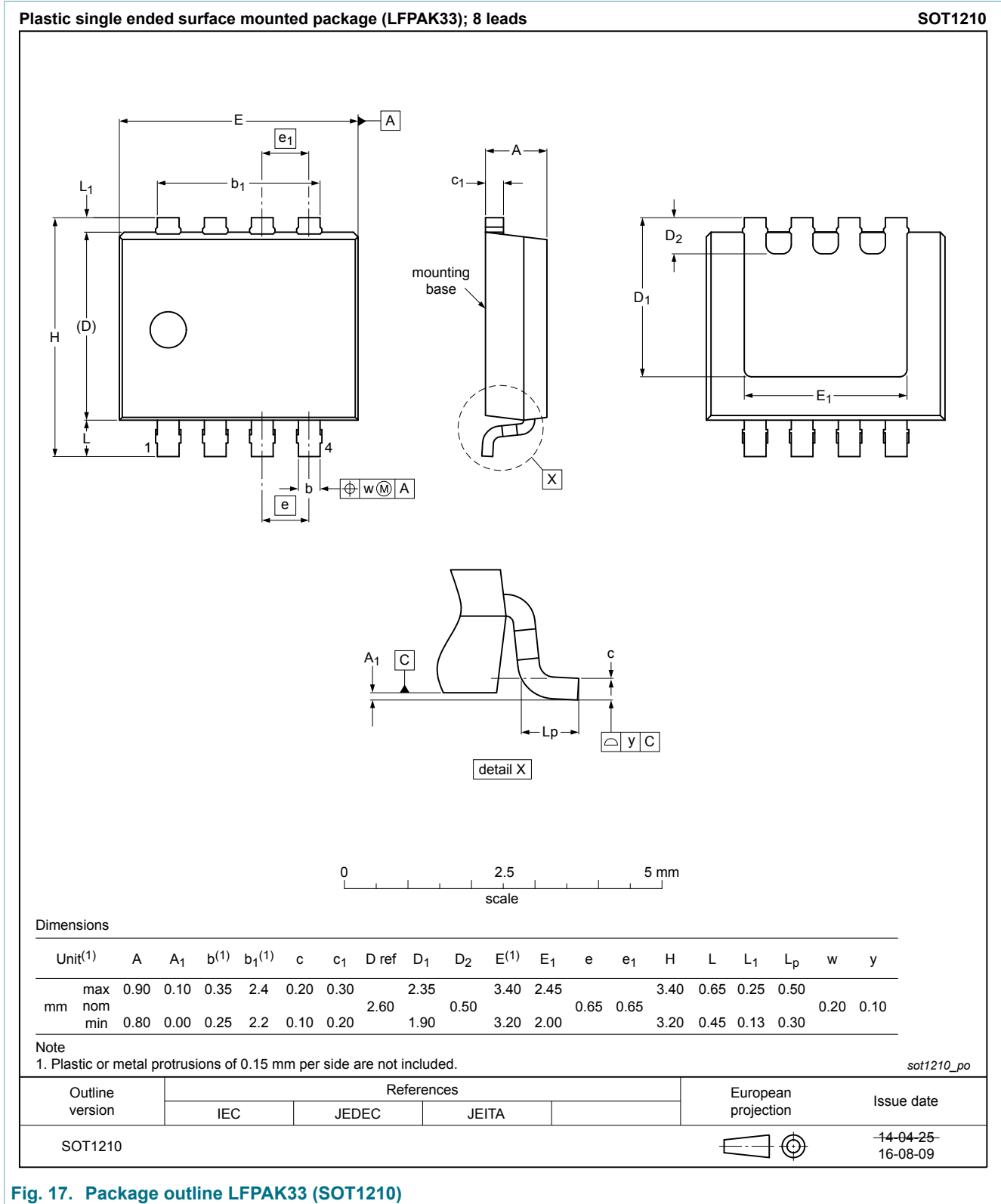


Fig. 17. Package outline LFAK33 (SOT1210)

12. Soldering

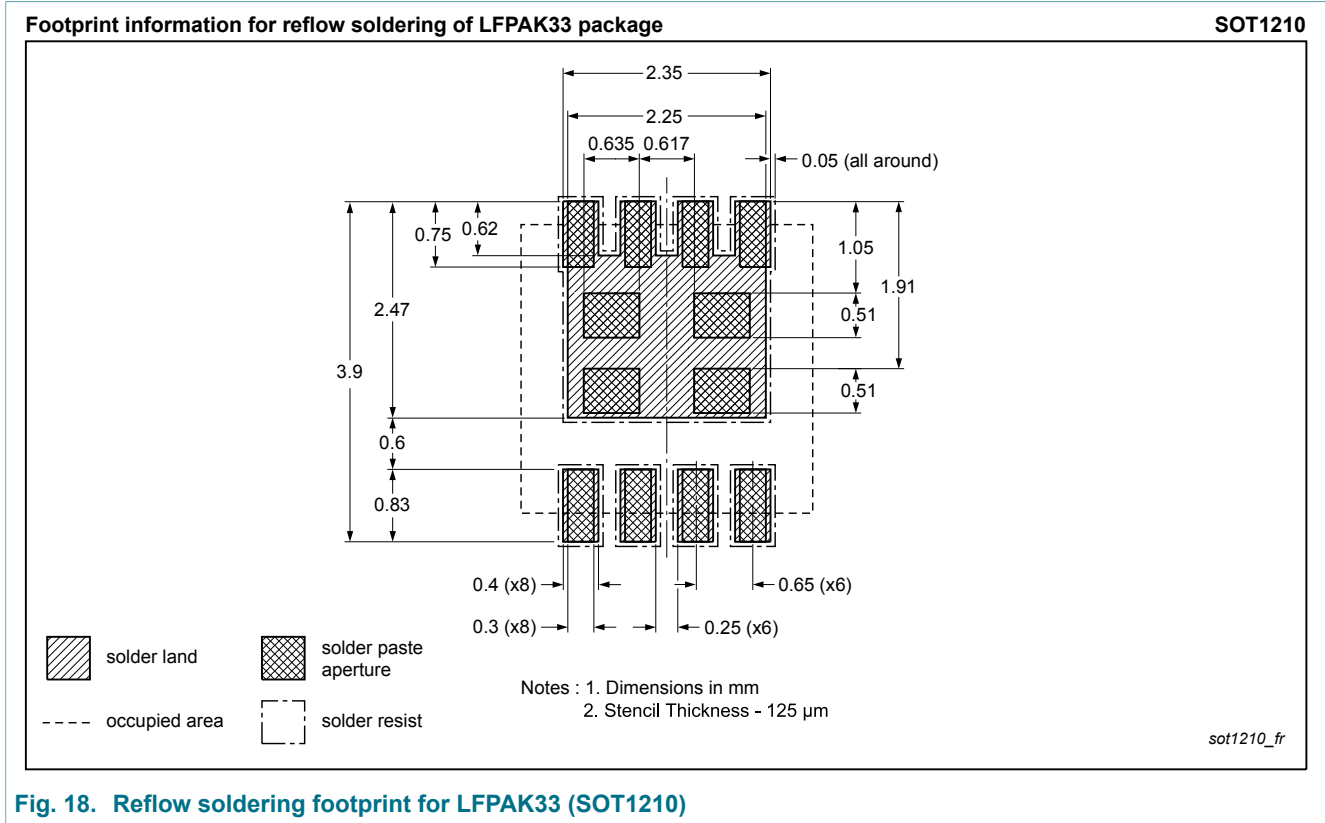


Fig. 18. Reflow soldering footprint for LPAK33 (SOT1210)

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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